# **General Purpose Transistor**

# **PNP Silicon**

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-416/SC-75 which is designed for low power surface mount applications.

### Features

• This is a Pb–Free Device

### **MAXIMUM RATINGS** (T<sub>A</sub> = $25^{\circ}$ C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current – Continuous	۱ <sub>C</sub>	-100	mAdc
Collector Current – Peak	۱ <sub>C</sub>	-200	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Total Device Dissipation, FR-4 Board (Note 1) T <sub>A</sub> = 25°C Derated above 25°C	P <sub>D</sub>	200 1.6	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ hetaJA}$	600	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T <sub>A</sub> = 25°C Derated above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	400	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

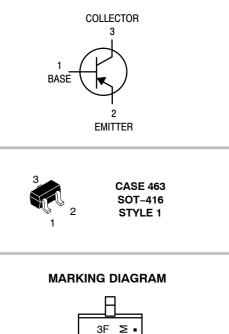
1. FR-4 @ min pad.

2. FR-4 @  $1.0 \times 1.0$  in pad.



# **ON Semiconductor®**

http://onsemi.com





3F = Device Code M = Date Code

= Date Code
= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

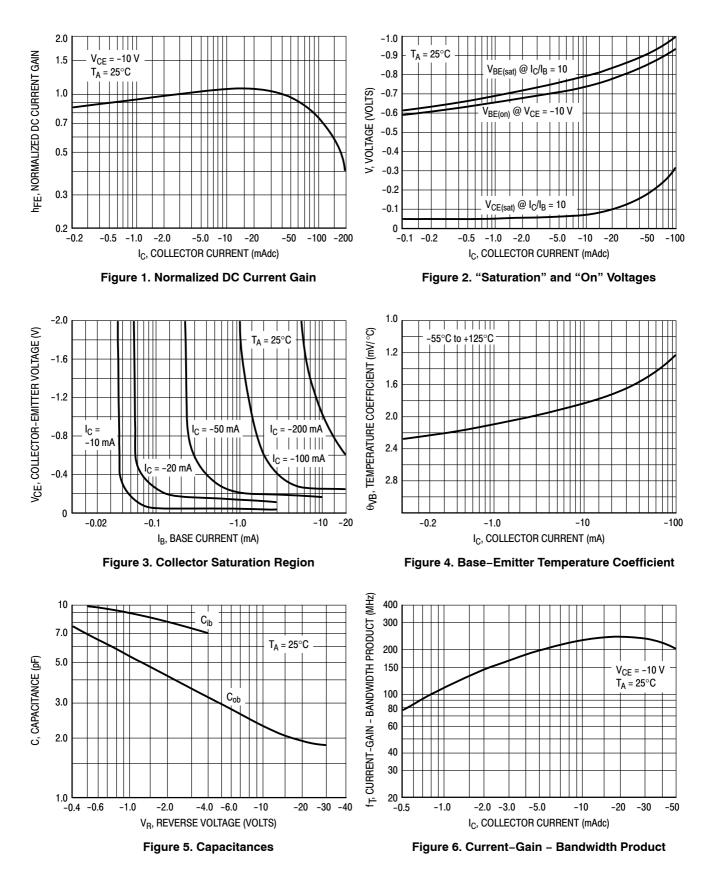
### **ORDERING INFORMATION**

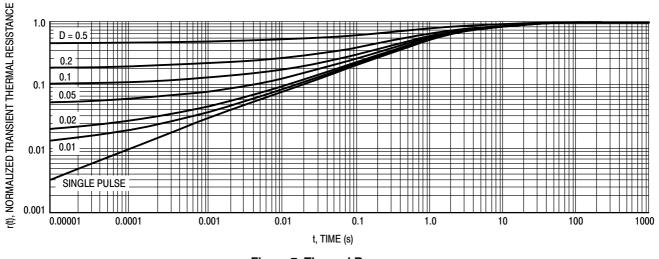
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

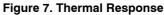
# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage $(I_{C} = -10 \text{ mA})$	V <sub>(BR)CEO</sub>	-45	_	-	V
Collector – Emitter Breakdown Voltage ( $I_C = -10 \ \mu A$ , $V_{EB} = 0$ )	V <sub>(BR)CES</sub>	-50	_	-	V
Collector – Base Breakdown Voltage $(I_C = -10 \ \mu A)$	V <sub>(BR)CBO</sub>	-50	_	-	V
Emitter – Base Breakdown Voltage $(I_E = -1.0 \ \mu A)$	V <sub>(BR)EBO</sub>	-5.0	_	-	V
Collector Cutoff Current (V <sub>CB</sub> = -30 V) (V <sub>CB</sub> = -30 V, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>			-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = −10 μA, V <sub>CE</sub> = −5.0 V) (I <sub>C</sub> = −2.0 mA, V <sub>CE</sub> = −5.0 V)	h <sub>FE</sub>	_ 220	150 290	_ 475	-
Collector – Emitter Saturation Voltage ( $I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$ )	V <sub>CE(sat)</sub>			-0.3 -0.65	V
Base – Emitter Saturation Voltage ( $I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$ )	V <sub>BE(sat)</sub>		-0.7 -0.9		V
Base – Emitter On Voltage ( $I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V}$ ) ( $I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ V}$ )	V <sub>BE(on)</sub>	-0.6 -		-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS	·				
Current – Gain – Bandwidth Product ( $I_C = -10$ mA, $V_{CE} = -5.0$ Vdc, f = 100 MHz)	fT	100	_	-	MHz
Output Capacitance ( $V_{CB} = -10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$ )	C <sub>ob</sub>	-	_	4.5	pF
Noise Figure (I <sub>C</sub> = -0.2 mA, V <sub>CE</sub> = -5.0 Vdc, R <sub>S</sub> = 2.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	-	_	10	dB

### **TYPICAL CHARACTERISTICS**







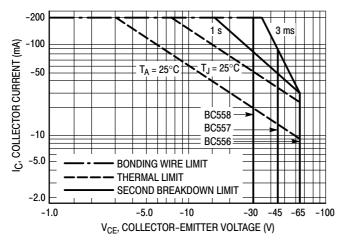


Figure 8. Active Region Safe Operating Area

The safe operating area curves indicate  $I_C-V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 8 is based upon  $T_{J(pk)} = 150^{\circ}C$ ;  $T_C$  or  $T_A$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 7. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

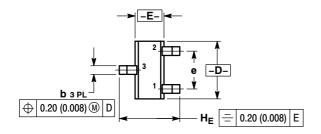
### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BC857BTT1G	SOT-416 (PB-Free)	3,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### PACKAGE DIMENSIONS

**SOT-416 (SC-75)** CASE 463 ISSUE F



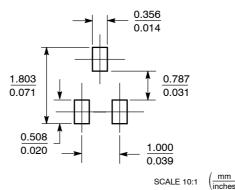
NOTES:

 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETER

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.061	0.063	0.065

**SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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